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Optoelectronic excitations and photovoltaic effect in strongly correlated materials

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Solar cells based on conventional semiconductors have low efficiency in converting solar energy into electricity because the excess energy beyond the gap of an incident solar photon is converted into heat by phonons. Here we show by *ab initio* methods that the presence of strong Coulomb interactions in strongly correlated insulators (SCI) causes the highly photo-excited electron-hole pair to decay fast into multiple electron-hole pairs via impact ionization (II). We show that the II rate in the insulating M_1 phase of vanadium dioxide (chosen for this study as it is considered a prototypical SCI) is two orders of magnitude higher than in Si and much higher than the rate of hot electron/hole decay due to phonons. Our results indicate that a rather broad class of materials may be harnessed for an efficient solar-to-electrical energy conversion that has been not considered before.

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Among several factors that practically limit solar cell efficiency is the fact that the excess energy of hot electrons, excited much above the semiconducting gap by absorbing a high energy solar photon, is taken away by lattice excitations within a time scale of the order of $10^{-13} - 10^{-12}$ seconds [1–3]. This is schematically illustrated in Fig. 1 (top): In *conventional semiconductors* the incident solar photon promotes an electron from the occupied valence band to the conduction band. The excess energy of the excited "hot" electron beyond the energy gap (the solar spectrum ranges from 0.5 eV to 3.5 eV) is converted into waste heat by phonon emission and the electron relaxes to its band edge within $10^{-13} - 10^{-12}$ seconds. If one chooses the material to have a large energy gap, solar photons with excess energy below the energy gap cannot excite electron hole pairs, and all excess energy is lost to phonons.

There are many ideas on how to solve this problem (for example, see Ref. 4 and Ref. 5). Following a recent suggestion[6], we will demonstrate in this paper, by means of *ab initio* methods, that if strongly correlated insulators (SCI), such as the transition metal oxides (TMOs), are used as a basis for photovoltaic applications, one may see high quantum efficiency. As illustrated in Fig. 1 (bottom) in *a strongly correlated insulator* the photo-excited electron (or hole) may utilize its strong Coulomb interaction (shown in figure by the red zig-zag line) with another valence electron to promote it to the conduction band, thus, creating a second electron-hole pair using the energy of the *same* solar photon. In a SCI, the localized electrons form an electronic system in which the residual effective electron-electron interaction is strong and can lead to a fast decay of the initially

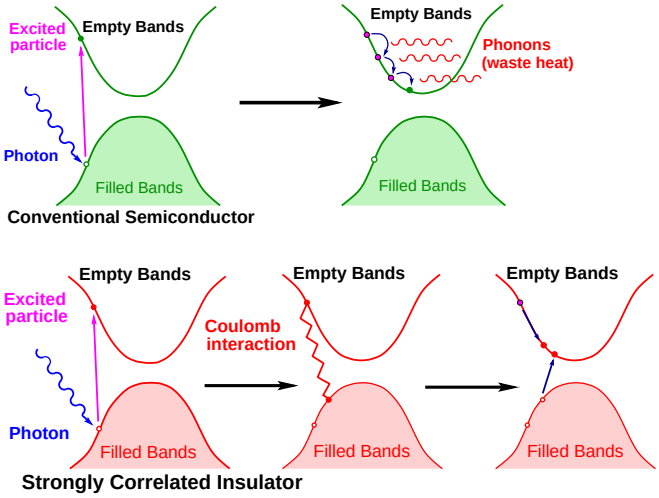

FIG. 1: The standard process in *conventional semiconductors* is shown above (green bands) while the expected process in *strongly correlated insulators* is shown below (red bands). See text for explanation.

photo-excited electron/hole pair into multiple electron-hole pairs [so-called impact ionization (II)] on a time-scale much faster than other decay processes. This clearly can lead to carrier multiplication, namely, the energy of a single incident photon is used to create multiple electron-hole pairs instead of creating phonons. This process, in Si and within the limits of the solar spectrum, takes place in about the same time-scale as the phonon relaxation processes.

Since an insulator is needed for such photovoltaic applications, it was further proposed[6] working at the simple model level that a Mott insulator, where such strong

correlations are present, could be used. However, all that is needed for this idea to work is the strong Coulomb interaction and the essence of the proposal is still applicable in the more general case of strongly correlated materials, where the insulating gap is not necessarily a Mott gap but of a some other origin; for example, while VO_2 is a strongly correlated material, the gap is believed to be due to a Peierls instability.[7–9] The possible increase of solar cell efficiency due to carrier multiplication through the impact ionization process has been proposed previously for traditional semiconductor nanocrystals.[4, 5] The first encouraging demonstration of the presence of multiple excitons in the photo-current has been demonstrated in a photovoltaic cell based on semiconductor nanocrystals[10]; however, the effect is not very strong. Thus, alternative materials showing promise for carrier multiplication upon solar illumination are still much sought-after.

In order to demonstrate that in SCI the II rate (IIR) is significantly enhanced we choose the room temperature phase of VO_2 (the M_1-phase) because VO_2 is considered a prototypical strongly correlated insulator with a lot of history surrounding it. We show that the residual electron-electron interaction in this material is indeed very strong. Furthermore, we show that the IIR is much larger than the rate characterizing phonon processes and in the region of the solar spectrum the IIR is orders of magnitude higher than that in Si. VO_2 is used only to demonstrate increased IIR in strongly correlated materials, corresponding to multiple exciton generation (MEG). It is not proposed as the optimal material for use in a photo-voltaic device due to other factors, some of which are discussed in our concluding remarks. The goal of the present paper is to show that this more general class of strongly correlated insulators should be explored experimentally to find the optimal material. Therefore, here, we claim that strongly correlated materials can be good candidates to focus the search for efficient photovoltaics. We particularly emphasize that a p-n junction has been very recently made[11] from the insulating M_1 phase of VO_2 (M_1-VO_2).

Multiple-carrier production due to impact ionization has not been the subject of experimental investigation in this family of materials. It is of immediate importance to have a computational *ab initio* scheme which is reliable to evaluate opto-electronic properties such as excitations, gaps, absorption, IIR and related properties for a given bulk or interface structure of TMOs. Many-body perturbation theory, such as the Bethe-Salpeter equation (BSE), is useful for accurately calculating the optical properties of traditional semiconductors.[12] However, it is an open question whether or not the BSE method based on well-established quasi-particle states and energies is able to provide qualitatively good results on the optical properties of the much less studied strongly correlated electron systems in TMOs such as M_1-VO_2.

As a first inevitable step in this direction, we study the optical properties of M_1-VO_2 by many-body perturbation techniques. We start with a self-consistent GW procedure (scGW)[14, 15] based on density functional theory in order to obtain quasi-particle energies and states (see Fig. 2a), which has given good results on similar materials[16], including strongly correlated f electron systems[17, 18]. This self-consistent procedure is the only *ab-initio* way to obtain consistent results, a good single particle gap and density of states for this system.[7] Then, we include the electron-hole interactions in quasiparticles via the BSE method and calculate the optical properties of VO_2.

We carry out density functional theory (DFT) calculations using the plane wave basis set (plane wave cutoff of 400 eV) with the projector augmented wave (PAW) method [19], as implemented within the VASP package.[20–23] The experimental geometry of M_1-VO_2 is used where the parallel direction of the lattice is defined along its a-axis according to the convention (see Supplementary for additional information). Either PBE[24] or HSE06[25] functionals are applied as a starting point for the self-consistent GW procedure as described in Ref. 7, in order to obtain quasi-particle energies *and* states. We include the vanadium 3p electrons as valence in the calculations which results in 46 valence band (occupied) states that we label by n_v. In the GW procedure, we use 146 conduction band (virtual) states that we label by n_c. The inclusion of only $3p$ vs. $3s$ electrons was checked at the level of G_0W_0 and no difference was found within ± 10 eV of the Fermi level. Based on a recent publication[26], one must be very careful with the convergence of the plane-wave basis set in PAW-based GW calculations. While the absolute value of the energy eigenvalues shows a significant change with number of bands and size of basis set, the energy difference between eigenvalues is much less sensitive to these parameters. For example, the size of our plane-wave basis set ($\sim$850 plane waves) is sufficient to produce a gap in the calculations presented in Ref. 26 accurate to about 3%. Additionally, the number of conduction bands used here is sufficient to converge the band gap in Ref. 26 to within 6% of the value produced when the fully convergent limit of the number of bands is reached. This is impossible to reach in the fully scGW scheme used here. Note that these estimates are based on G_0W_0 calculations, and produce corrections far smaller than those obtained with scGW. For the optical properties we solve the BSE by diagonalizing the well-known electron-hole pair Hamiltonian[12]. For VO_2, we used 26 occupied and unoccupied bands, on a $5\times5\times5$ k-point mesh in the BSE calculations presented here. For Silicon, we used 4 occupied and 8 unoccupied bands, on a $12\times12\times12$ k-point mesh, with the experimental geometry. We checked in detail that these sizes are large enough to produce converged results. For details on convergence and implementation, please see the

Supplementary Material[27].

By applying the above discussed implementation of the BSE method (see Supplementary[27]) on top of scGW quasiparticle states obtained in Ref. 7, we are able to achieve excellent agreement with the experimental dielectric function[13] of Si (see Fig. S3 of the supplementary material[27]). This indicates that the current approach is a state-of-the-art *ab initio* method to be used for optical properties.

The major features in the calculated reflectance spectra of VO_2 broadly agree with available experimental data for a wide range of excitation energies up to 10 eV:[28, 29] The main peaks are accurately reproduced at about 0.7 eV, 3.5 eV and 8.0 eV in the parallel direction and at about 0.7 eV, 3.2 eV and 7.9 eV in the perpendicular direction (see Fig. 2). We note that our results are valid at T=0K but that the inclusion of the electron-phonon interaction, which might have a measurable effect in the optical spectrum observed at room temperature, is beyond the scope of the paper. Nevertheless, we conclude that the BSE method is able to provide good results on the absorption properties. Next, we focus our discussion on the threshold of absorption (optical gap) which is the lowest energy excitation.

The optical gap in the BSE calculation appears at 0.26 eV valid at T=0K. The absorption spectrum is recorded at room temperature, so that it is not obvious where the experimental onset of absorption is. Nevertheless, one may observe that the absorption starts to rise at ∼0.4 eV in the bulk [28–30] while in thin films it rises at ∼0.5 eV.[30–32] Photo-emission data indicates a fundamental single particle gap of ∼0.6 eV, in agreement with our scGW calculation.[7] Thus, the binding energy of the exciton is ∼0.2 eV. In the scGW calculation[7] the calculated fundamental direct gap is 0.63 eV, thus, the BSE exciton binding energy is ∼0.37 eV. Therefore, both the calculated optical gap and the binding energy of the exciton agree reasonably well with the experiment. We note that the optimal band gap of high IIR absorber materials for solar cell applications is about 0.8 eV [33], which further reduces toward ∼0.3 eV when solar concentrators are applied.[34] This value lies close to the calculated optical gap of VO_2.

Next, we study the role of the electron-electron interaction by looking at the convergence of the optical gap as a function of the number of valence bands (see Fig. 2b). We find that the optical gap converges only when we include a large number of valence bands $n_v = 26$ from the top of valence band where these occupied bands are ∼10 eV deep. This suggests that the Coulomb-interaction between the quasi-particles is very strong. We believe that this may be due to the pronounced localized nature of the $d_{x^2-y^2}$ orbitals[7] and the strong electron correlation arising from the charge localization. While this material is found to be a Peierls and not a Mott insulator[8, 9], the conclusions of Ref. 6 are still applicable here: the screened Coulomb interaction between electrons and holes, which is found to be very strong in M_1-VO_2, might cause a high impact ionization rate, leading to multi-exciton generation upon high-energy excitation as explained in Fig. 1.

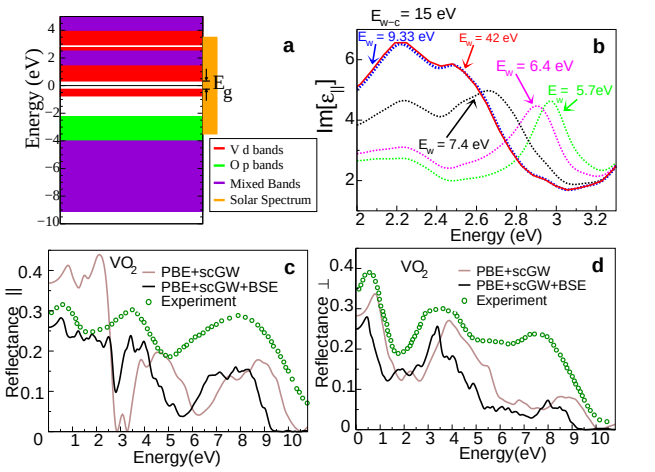

FIG. 2: **a)** Schematic diagram on the bands of highly correlated electrons (vanadium d-orbitals) and conventional bands (s,p-orbitals). The origin is set in the middle of the fundamental band gap. E_g=0.63 eV is the calculated fundamental direct gap of M_1-VO_2. **b)** The convergence of the first absorption peak by the BSE method as a function of the valence band width (E_w measured from the top of the valence band) included in the BSE calculation. **(c,d)** The experimental data taken from Ref. [28] for the reflectance of M_1-VO_2 for polarization parallel (**c**) and perpendicular (**d**) directions, is compared with the results of PBE+scGW+BSE calculation. The PBE+scGW spectra are given to show the exciton effects captured by BSE method. The structure of M_1-VO_2 and the definition of directions are given in the Supplementary Material[27].

In order to demonstrate that this large effective Coulomb interaction can play a significant role in enhancing the IIR, next, we present our results for the IIR on Si and VO_2. An estimate of the IIR can be obtained using the self-energy calculated from the scGW wave functions, similar to earlier work using G_0W_0.[35] The IIR $\tau^{-1}_{\vec{k}n}$ is calculated from the self-energy as:

$$\tau^{-1}_{\vec{k}n} = \frac{2Z_{\vec{k}n}}{\hbar}|\mathrm{Im}\,\Sigma_{\vec{k}n}|\,;\; Z_{\vec{k}n} = \left(1 - \mathrm{Re}\frac{\partial\Sigma_{\vec{k}n}(\omega)}{\partial\omega}\Big|_{\epsilon_{\vec{k}n}}\right)^{-1} \quad (1)$$

where $\vec{k}$ and n are k-point and band indices. When n band indices are running for valence bands then they correspond to the recombination to the hole-initiated biexcitons, otherwise to the electron-initiated biexcitons.[36] For the self-energy calculations, we use the same parameters as in the scGW calculations described earlier. Further details on the calculation are given in the Supplementary Materials[27].

We can give an indication that the IIR for VO_2 is

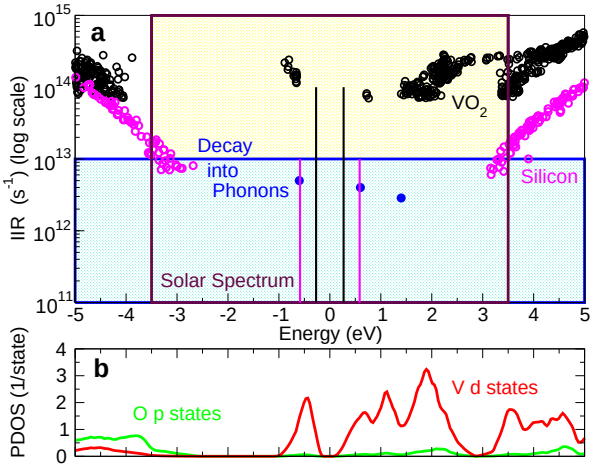

FIG. 3: **a)** The IIR of Si and M_1-VO_2 within our method. Additionally, the regions of the solar spectrum and rate of decay into phonon modes[2] are outlined for clarity. Points where the decay rate of electrons to phonons has recently been calculated [1] are highlighted in blue. The data points in Si and in VO_2 for IIR below certain cutoffs are not sufficiently accurate (for details see Supplementary material[27]), thus, we do not show those points here. The band gaps for Si and VO_2 are indicated by vertical lines at approximately 1.2 and 0.6 eV respectively. **b)** Decomposition of IIR to the corresponding bands of M_1-VO_2. The highly correlated bands are labeled by red curves originated from vanadium d-orbitals while the conventional bands in green are from the oxygen p-orbitals.

much higher than that of Si within the solar spectrum by comparing our results on Si and VO_2. As can be seen in Fig. 3, the IIR on VO_2 within the region of the solar spectrum is at least two orders of magnitude higher than that on Si. Additionally we find, in agreement with the prediction,[6] that the IIR for VO_2 is significantly higher (2-3 orders of magnitude) than the rate of decay into phonons, which is required in order for the impact ionization to be effective relative to phonon processes. Particularly, the hole-initiated biexcitons[36] associated with the sub-bands of d-electrons have an increased IIR while the p-bands show an IIR similar to the traditional Si semiconductor bands. This clearly demonstrates that the highly correlated electrons indeed provide a high impact ionization rate which is the basis of multiple exciton generation upon solar illumination. Here, we demonstrated that effective carrier multiplication should occur in M_1-VO_2. We conclude that strongly correlated and particularly, related TMO materials, can be very promising for probing enhanced multiple exciton generation in 3D solids.

A recent measurement on mono-crystalline monobeams of VO_2 gives us hope for efficient separation of photo-excited carriers in SCI. Contrary to expectations, long recombination lifetime of the order of microseconds upon laser illumination was found of the extracted carriers.[37] This surprisingly slow carrier recombination may be understood by the fact that certain optical transitions across the d-sub-bands of VO_2 are forbidden. We also find that typical velocities of electrons or holes of the VO_2 bands near the Fermi surface are very high, a fact which when combined with the high VO_2 dielectric constant leads to large separation distances between the photo-excited electron-hole pairs within very short time scales. However, VO_2 may not be the appropriate material to use for photovoltaic applications for other reasons. For example, upon moderate heating (which occurs naturally upon solar illumination) it undergoes a metal insulator transition. In addition, VO_2 appears to be "self-doped" with a relatively high n-type carrier density in the pure gapped M_1 phase. However, the main point of the present paper is not to promote VO_2 as the material of choice for photovoltaic applications. We have used VO_2 simply because it is a prototypical material where strong electron correlations play an important role and we showed that the IIR is significantly increased. The high IIR which is confirmed, here, to occur in SCI at such low energy in the solar spectrum gives solid indication that the multiple-carrier excitation effect would be important when SCI are used as basis for solar cells.[6] From within this broad class of materials one should select for further investigation those which exhibit other properties which are promising for photovoltaic applications, including long carrier lifetime, small recombination rate[37] and enhanced mobility.

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